## Abstract

A semiconductor wafer back grinding method which grinds, by grinding means, the back of a semiconductor wafer having a plurality of circuits formed on the face thereof and having an outer peripheral edge of a nearly semispherical sectional shape, thereby bringing the semiconductor wafer to a predetermined thickness. Pretreatment for forming the outer peripheral edge of the semiconductor wafer into a flat surface making an angle $\theta$, such that 80 degrees $\leq \theta \leq$ 100 degrees, preferably 85 degrees $\leq \theta \leq$ 95 degrees, with respect to the back of the semiconductor wafer is performed before the back of the semiconductor wafer is ground.




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